



## T4M10T600B(LS)

# TRIACS SILICON BIDIRECTIONAL THYRISTORS

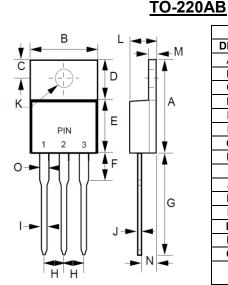
# TRIACS 4 AMPERES RMS 600 VOLTS

#### **FEATURES**

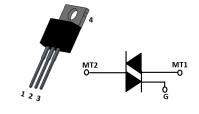
- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- High Immunity to dv/dt 50V/µs Minimum at +125°C
- Minimum and Maximum Values of I<sub>GT</sub>, V<sub>GT</sub> and I<sub>H</sub> Specified for Ease of Design on
- On-State Current Rating of 4 Amperes RMS at +100°C
- High Surge Current of 40 Amperes
- Rugged, Economical TO-220AB Package
- Operational in Three Quadrants: Q1, Q2, and Q3
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **MECHANICAL DATA**

- Package: TO-220AB
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.07 ounces, 2.0 grams (Approximate)



TO-220AB			
DIM.	MIN. MAX		
Α	14.22	15.88	
В	9.65	10.67	
С	2.54	3.43	
D	5.84	6.86	
Е	8.26	9.28	
F		6.35	
G	12.70	14.73	
Н	2.29	2.79	
ı	0.51	1.14	
J	0.40	0.67	
K	3.53Ø	4.09Ø	
L	3.56	4.83	
М	1.14	1.40	
N	2.03	2.92	
0	1.17	1.37	
All Dimensions in			
millimeter.			



PIN ASSIGNMENT		
1	Main terminal 1	
2	Main terminal 2	
3	Gate	
4	Main terminal 2	

#### **MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at +25°C ambient temperature unless otherwise specified.

#### **MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Peak repetitive off-state voltage $(T_J = -40 \text{ to } +125^{\circ}\text{C}, \text{ sine wave, } 50 \text{ to } 60\text{Hz}; \text{ gate open)}$	V <sub>DRM</sub> V <sub>RRM</sub>	600 600	V
On-stage RMS current (full sine wave 50 to 60Hz, T <sub>C</sub> = +100°C)	I <sub>T(RMS)</sub>	4.0	А
Peak non-repetitive surge current (one full cycle 60Hz, T <sub>J</sub> = +25°C)	I <sub>TSM</sub>	40	Α
Circuit fusing consideration (t = 8.3ms)	l <sup>2</sup> t	6.6	A <sup>2</sup> s
Operating junction temperature range	TJ	-40 to +125	°C
Storage temperature range	T <sub>STG</sub>	-40 to +150	°C

#### **Notes**

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



#### **OFF CHARACTERISTICS**

PARAMETER		SYMBOL	MAX	UNIT
Peak repetitive forward or reverse blocking current	$T_J = +25^{\circ}C$	I <sub>DRM</sub>	10	μA
(Vak = rated V <sub>DRM</sub> and V <sub>RRM</sub> , gate open)	$T_J = +125^{\circ}C$	I <sub>RRM</sub>	2	mA

#### **ON CHARACTERISTICS**

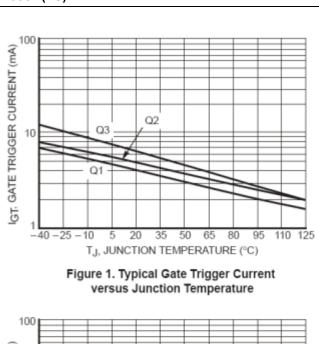
PARAMETER	SYMBOL	MAX	UNIT
Peak forward on-state voltage (I <sub>TM</sub> = ±6A @ t <sub>P</sub> ≤ 2.0ms, duty cycle ≤ 2%)	Vтм	1.6	V
Gate trigger current $(V_D = 12V, R_L = 100\Omega)$	I <sub>GT1</sub> I <sub>GT2</sub> I <sub>GT3</sub>	10 10 10	mA
Gate trigger voltage $(V_D = 12V, R_L = 100\Omega)$	V <sub>GT1</sub> V <sub>GT2</sub> V <sub>GT3</sub>	1.3 1.3 1.3	V
Holding current (V <sub>D</sub> = 12V, initiation current = ±200mA, gate open)	I <sub>H</sub>	15	mA
Latching current $(V_D = 12V, I_G = 10mA)$		30 30 30	mA

#### **DYNAMIC CHARACTERISTICS**

PARAMETER	SYMBOL	MIN	UNIT
Critical rate of rise of off-state voltage $V_{AK} = 67\%$ rated $V_{DRM}$ , exponential waveform, gate open $T_{J} = +125$ °C	dv/dt	50	V/µs



## RATING AND CHARACTERISTIC CURVES T4M10T600B(LS)



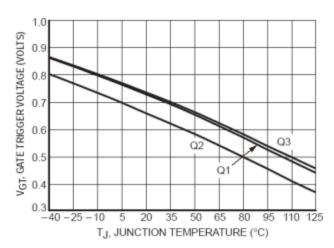


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

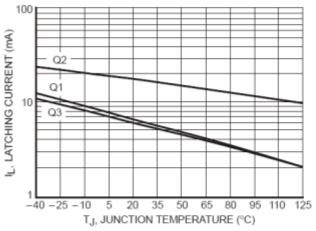


Figure 3. Typical Latching Current versus Junction Temperature

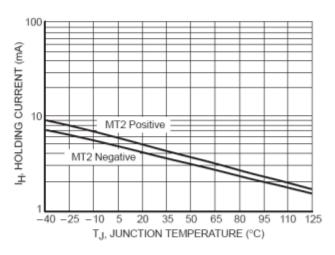


Figure 4. Typical Holding Current versus Junction Temperature

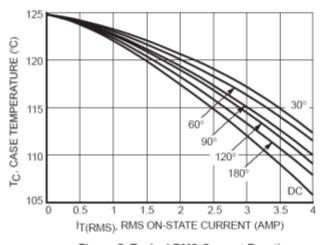


Figure 5. Typical RMS Current Derating

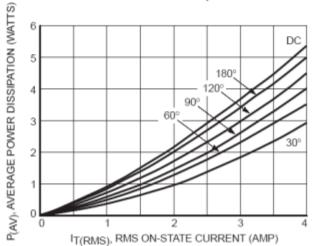
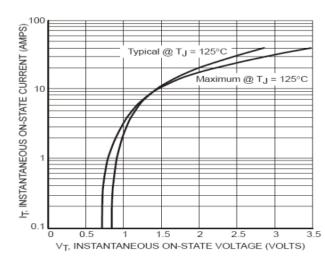


Figure 6. On-State Power Dissipation



# RATING AND CHARACTERISTIC CURVES T4M10T600B(LS)



(t) TRANSIENT THERMAL RESISTANCE (NORMALIZED) 0.01 1 10 100 1000 10000 t, TIME (ms)

Figure 7. Typical On-State Characteristics

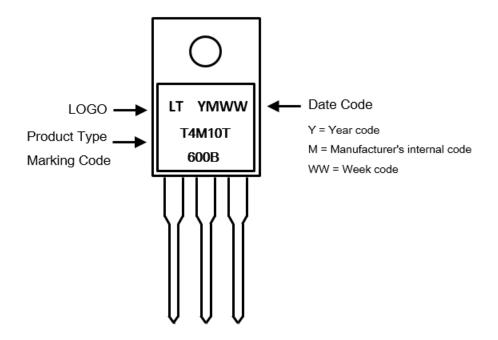
Figure 8. Typical Thermal Response



## **Ordering Information:**

Part Number	Packago	Package Packing Qty. Carr	
	rackage		
T4M10T600B	TO-220AB	50pcs	Tube

## **Marking Information:**





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